INFORMATION DISCLOSURE STATEMENT BY APPLICANT Applicant: MANABE et al. Applicant: MANABE et al. Applicant: MANABE et al. Applicant: MANABE et al. Filing Date: October 2, 2000 Examiner: S. Mulpuri Group Art Unit: 2812 U.S. PATENT DOCUMENTS Examiner' Document S. Mulpuri Group Art Unit: 2812 U.S. PATENT DOCUMENTS Examiner' Document Number MM/YYYY (Family Name of First Inventor) Class Sub Filing Class Date	(PW FORM Patent	epartr PAT-	nent of Commerce			MOY	2 8 2001	JC147 30/2	Ætty. Dkt. No.				Clien	t Ref.		
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